

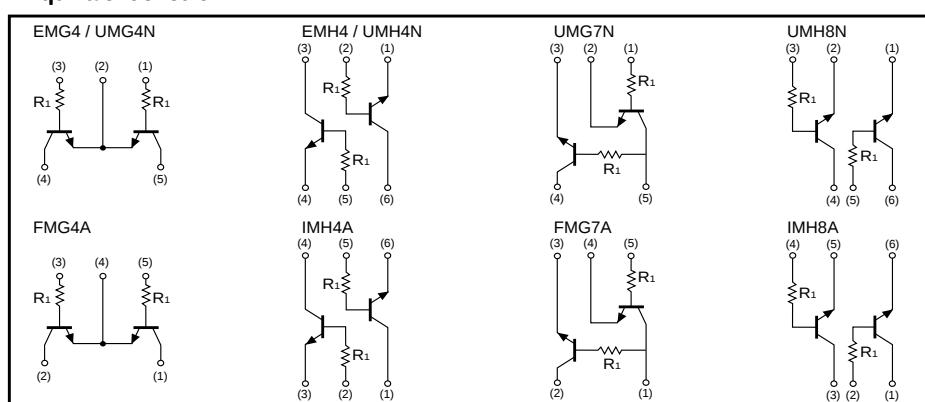
General purpose (dual digital transistors)

EMG4 / EMH4 / UMG4N / UMG7N / UMH4N / UMH8N FMG4A / FMG7A / IMH4A / IMH8A

●Features

- 1) Two DTC114T chips in a EMT or UMT or SMT package.

●Equivalent circuit



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CB0}	50	V
Collector-emitter voltage	V_{CE0}	50	V
Emitter-base voltage	V_{EB0}	5	V
Collector current	I_C	100	mA
Power dissipation	EMG4 / EMH4 / UMG4N / UMG7N / UMH4N / UMH8N FMG4A / FMG7A / IMH4A / IMH8A	150(TOTAL)	mW *1
		300(TOTAL)	
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55~+150	°C

*1 120mW per element must not be exceeded.

*2 200mW per element must not be exceeded.

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CB0}	50	—	—	V	$I_C=50\mu A$
Collector-emitter breakdown voltage	BV_{CE0}	50	—	—	V	$I_C=1mA$
Emitter-base breakdown voltage	BV_{EB0}	5	—	—	V	$I_E=50\mu A$
Collector cutoff current	I_{CB0}	—	—	0.5	μA	$V_{CB}=50V$
Emitter cutoff current	I_{EB0}	—	—	0.5	μA	$V_{EB}=4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	0.3	V	$I_C/I_E=10mA/1mA$
DC current transfer ratio	h_{FE}	100	250	600	—	$V_{CE}=5V, I_C=1mA$
Transition frequency	f_T	—	250	—	MHz	$V_{CE}=10V, I_E=-5mA, f=100MHz$ *
Input resistance	R_1	7	10	13	k Ω	—

*Transition frequency of the device.

Transistors

● Package, marking, and packaging specifications

[illegible]

● **External dimensions** (Units : mm)

